

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

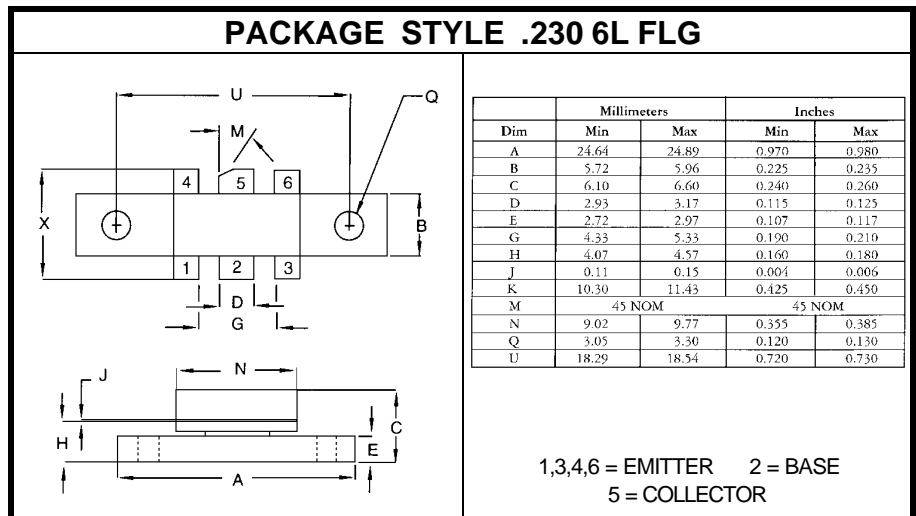
The **ASI SD1425** is Designed for Class AB Linear Base Station Applications in the 800-900 MHz Frequency Range.

FEATURES INCLUDE:

- Gold Metalization
- Input Matching
- Common Emitter
- Emitter Ballast Resistors

MAXIMUM RATINGS

I_C	5.0 A
V_{CB0}	50 V
V_{CES}	45 V
P_{DISS}	43 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
q_{JC}	3.0 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 100 mA	50			V
BV_{CEO}	I _C = 40 mA	25			V
BV_{CER}	I _C = 50 mA R _{BE} = 22 Ω	50			V
BV_{EBO}	I _E = 10 mA	3.5			V
I_{CB0}	V _{CB} = 24 V			2.0	mA
h_{FE}	V _{CE} = 10 V I _C = 200 mA	20		100	---
C_{ob}	V _{CB} = 24 V f = 1.0 MHz		40	50	pF
P_{out}	V _{CC} = 24 V P _{in} = 5.3 W f = 960 MHz	30			W
G_p		7.5			dB
h_C		45	50		%



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